



D. Thin Film Process Technology 분과

2019년 2월 15일(금), 11:00-12:30

Room F (실버홀, 5층)

[FF2-D] Device Fabrication II

좌장: 전우진 교수(경희대학교), 박민혁 교수(부산대학교)

FF2-D-1 11:00-11:15	Improvement of Ferroelectric Field-Effects Assisted by Metal-Ferroelectric-Metal-Insulator-Semiconductor Structures Using Al-Doped HfO₂ Thin Film So-Yeong Na, So-Jung Yoon, and Sung-Min Yoon <i>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University</i>
FF2-D-2 11:15-11:45	[초청] Ferroelectricity in Hafnia Based Thin Films Min Hyuk Park <i>School of Materials Science and Engineering, Pusan National University</i>
FF2-D-3 11:45-12:00	New Class of Field-Effect Transistor with Two-Dimensional Electron Gas Using Atomic-Layer-Deposited Al₂O₃/TiO₂ Ultrathin (<10 nm) Film Heterostructure Tae Jun Seok ¹ , Yuhang Liu ¹ , Hae Jun Jung ² , Soo Bin Kim ² , Dae Hyun Kim ³ , Sung Min Kim ² , Jae Hyuck Jang ⁴ , Deok-Yong Cho ⁵ , Sang Woon Lee ² , and Tae Joo Park ^{1,3} ¹ <i>Department of Materials Science and Chemical Engineering, Hanyang University,</i> ² <i>Department of Energy Systems Research and Department of Physics, Ajou University,</i> ³ <i>Department of Advanced Materials Engineering, Hanyang University,</i> ⁴ <i>Center for Electron Microscopy Research, KBSI,</i> ⁵ <i>IPIT and Department of Physics, Chonbuk National University</i>
FF2-D-4 12:00-12:15	Low-Energy and Highly Reliable Multi-Bit Performance by Fully “Erase-Free” Operation in a HfO₂-Based Resistive Switching Device Jin Joo Ryu ^{1,2} , Kanghyeok Jeon ^{1,2} , Seungmin Yeo ¹ , Chunjoong Kim ² , and Gun Hwan Kim ¹ ¹ <i>Division of Advanced Materials, KRICT,</i> ² <i>Department of Materials Science and Engineering, Chungnam National University</i>
FF2-D-5 12:15-12:30	Turn-on Characteristics of Organic Resistive Memory Devices under a Constant Voltage Stress Woocheol Lee, Youngrok Kim, Younggul Song, Daekyoung Yoo, Keehoon Kang, and Takhee Lee <i>Department of Physics and Astronomy, Seoul National University</i>